



中国科学院高能物理研究所
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Weekly Meeting

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Vertex Specification

- CEPC Reference Detector(AGORA)
 - Spatial resolution $< 5 \mu\text{m}$
 - Time stamp precision $< 100 \text{ ns}$
 - Power Consumption in sensitive area $< 40 \text{ mW/cm}^2$
 - Higgs & low-luminosity Z operation
 - Maximum hit rate expected $\sim 39 \text{ MHz/cm}^2 @ r_{\text{min}} = 11 \text{ mm}$

Table 4.2: Vertex Detector Design Parameters

Parameter	Design
Spatial Resolution	$\sim 5 \mu\text{m}$
Detector material budget	$\sim 0.8\% X_0$
First layer radius	11.1 mm
Power Consumption	$< 40 \text{ mW/cm}^2$ (air cooling requirement)
Time stamp precision	100 ns
Fluence	$\sim 2 \times 10^{14} \text{ Neq/cm}^2$
Operation temperature	$\sim 5^\circ\text{C}$ to 30°C
Readout electronics	Fast, low-noise, low-power
Mechanical Support	Ultralight structures
Angular Coverage	$ \cos \theta < 0.99$

Synergy with FCC-ee

- FCC-ee Vertex detector
 - **High-luminosity Z operation**
 - Maximum hit rate > 200 MHz/cm² @ $r_{\min}=11.7$ mm
 - Maximum hit rate > 100 MHz/cm² @ $r_{\min}=13.7$ mm
- CEPC-stitching design maximum readout speed up to 43.3 MHz per RSU
 - constrained by the RSU power 38 mW/cm²

Projects for FCC-ee vertex detector, Dominik Dannheim
Detector background in vertex detector, Armin Ilg
@ FCC week 2026, Helsinki

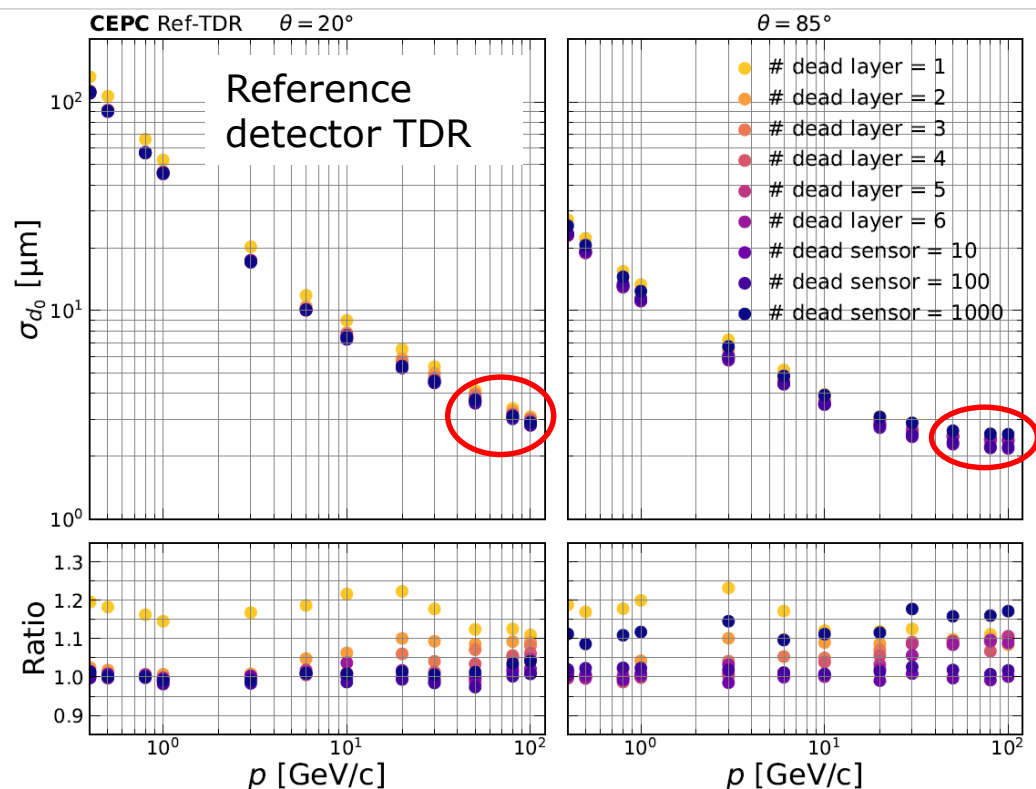
Table 4.9: Estimates of power consumption of one RSU. All values are for 27 °C temperature and 1.2 V power supply voltage.

Components	Pixel Analog	Pixel Digital	Biasing Block	Matrix Readout	Data Interface	RSU Total
Power [mW]	36	30	8	40	17	131

Mitigation to the high hit rate

- Keep CEPC-stitching design not changed
 - Increase $r_{\min}$ and optimize layer geometry for FCC-ee
 - Rectangular pixel to improve single point resolution at $r\phi$ direction $< 3 \mu\text{m}$ $\rightarrow$ compensate the loss for high momentum tracks (and FCC-ee also assumes $3 \mu\text{m}$)

Performance under sensor failure scenarios



$$\sigma_{r\phi} = a \oplus \frac{b}{p(\text{GeV}) \sin^{3/2} \theta}$$

Bread down the specification

- Pixel pitch: 16 x 30 μm
 - Analog front-end 16 x 16 μm , pixel logic and readout 14 x 16 μm
- Time precision: 100 ns (σ_t)
 - Time walk 300 ns (peak-peak) + clock sampling 50 ns (peak-peak)
- Average power: <**100 mW/cm²** (total power 160 mW) for the first submission
 - Analog Front-end 80 mW, digital logic 10 mW, data readout 60 mW
 - DAC 2 mW, LVDS 3 mW, analog buffer 3 mW
 - Other 2 mW

Pixel sensor process

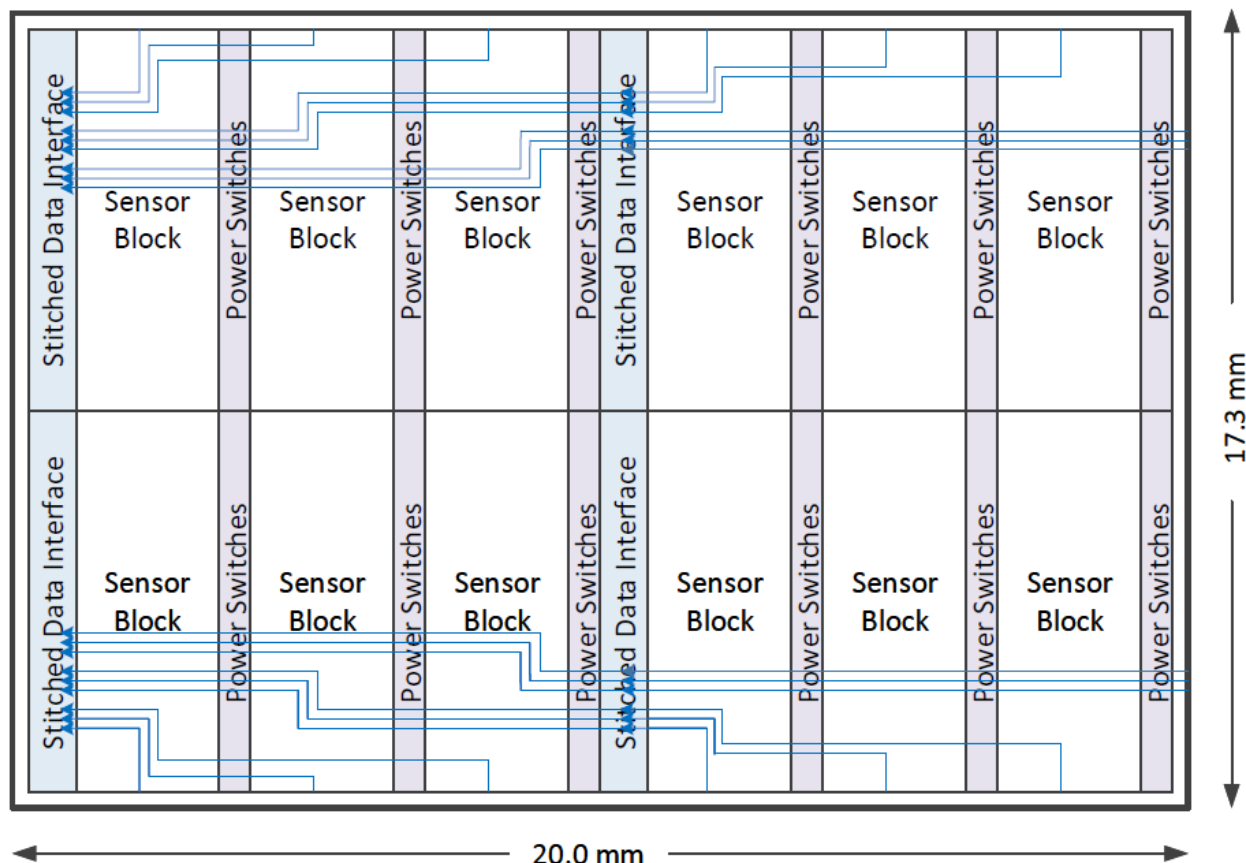
Ying Zhang, Zhijun Liang

- 90 nm CIS process, domestic foundry
 - **Mature production line**
 - **Quadruple-well**
 - **Support High-resistivity epitaxial layer**
 - Custom implant not allowed yet, needed for radiation hardness
- Contacting the foundry via an agent
 - PDK provided, 5 metal layers
 - Qualified HR wafers are under investigation
 - Engineering run only
 - Quotation will be provided based on the device choice

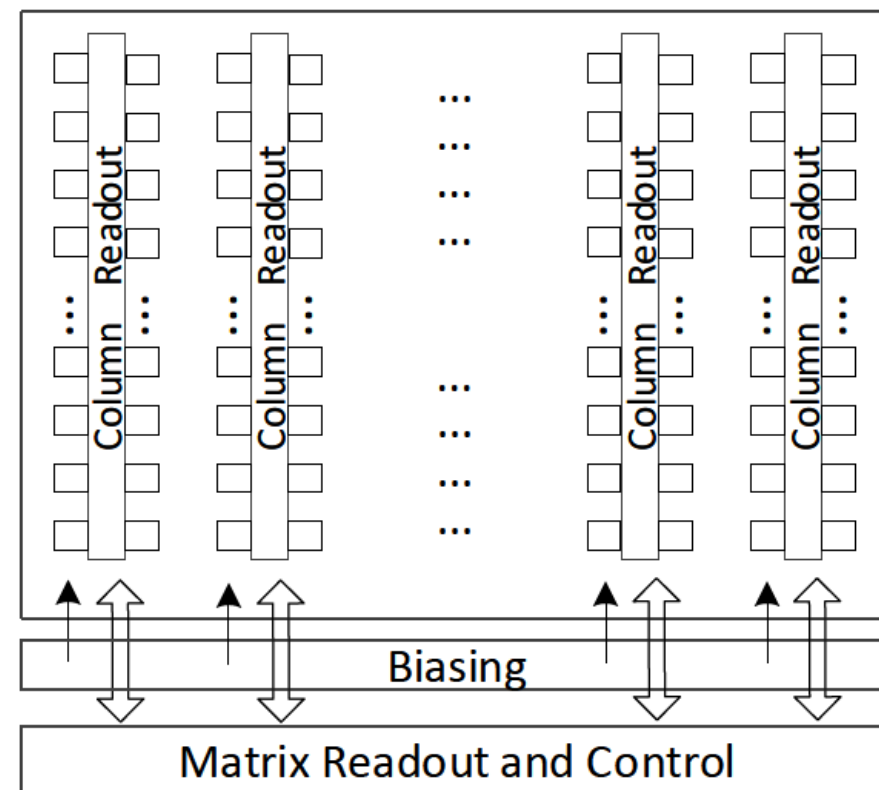
Validation of process

- Only Sensor Block for this submission
 - Compatible with the **Stitched sensor prototype design** (Reference Detector TDR)

top-level floor plan of a RSU (Repeated Sensor Unit)

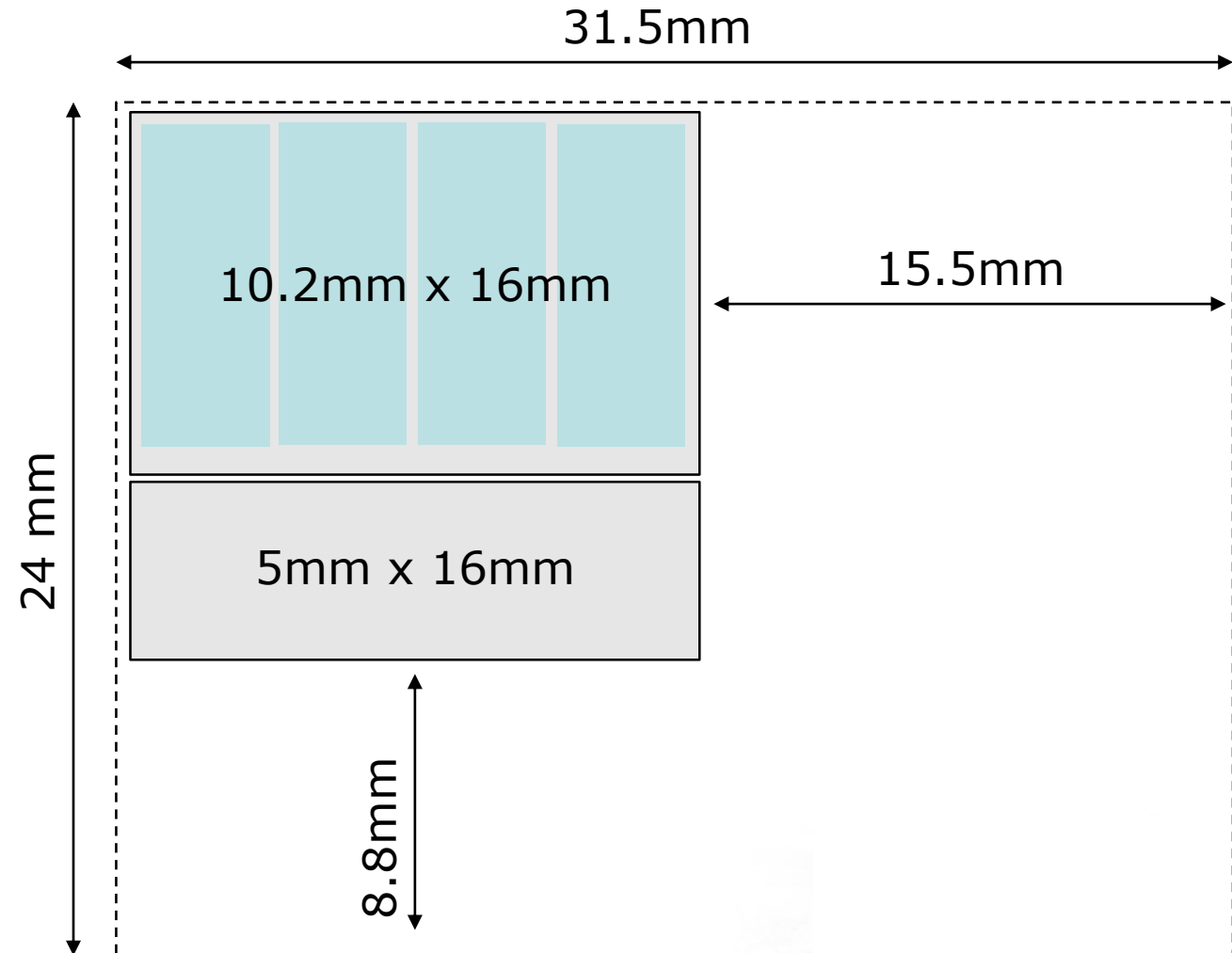


Architecture of the Sensor Block



Preliminary floor plan

- Maximum Mask Area: 24mm x 31.5mm
- Estimated design Area: 10.2mm x 16mm
 - Pixel pitch 16um x 30um
 - Matrix height 16um x 512行 = 8.192 mm
 - Matrix width 30um x 512列 = 15.36 mm
 - 4 sensor blocks
 - Peripheral + Pad height 2mm
- Independent test circuit module
 - 5mm x 16mm



Pixel Sensor Task Assignment

- Team members from the past TaichuPix and JadePix team

Task	Responsible person	Affiliation
Integration and verification	Yunepng Lu & Han Yu	IHEP
Process and analog front-end	Ying Zhang	IHEP
Matrix readout logic	Tianya Wu & Tong Li	NCU
Peripheral data readout	Xiaoming Wei & Student	NWPU
LVDS	Ping Yang & Student	CCNU
DAC	Ping Yang & Baoshu Hao	CCNU
Negative biased PAD	Ping Yang & Student	CCNU
Analog buffer	Hao Xiong	IHEP
PLL & Serializer & CML	Ping Yang & Quanwei Hu	CCNU
ASIC consultant	Wei Wei	IHEP
TCAD	Bo Liu, Ziyang Liu, Ying Zhang, Zhijun Liang	NKU & IHEP

Key points of design

- Analog front-end: TN, FPN, Time walk, power (ongoing)
- Logic analysis on FastOR signal and desertion
 - FastOR assertion and Freeze function (见郁晗报告)
 - FastOR desertion and readout debug (见邓思琪的分析)
- Understanding and definition of time stamp precision
 - Key contributor identified (见郁晗报告)
- Timing, power and area optimization on peripheral readout (to start)
- Static power analysis on full chip (in plan)
- Testability (in plan)
 - Single module verification
 - Avoid single-point failure in the signal chain

Schedule

- Tape-out in March 2027 (Preliminary plan, 9 months)
 - Scheme Design – 8 weeks, mid-July
 - Scheme Review – 1 week, late July
 - Module Design – 4 weeks, late August
 - Schematic Review – 1 week, mid-September
 - Layout Design – 8 weeks, mid-November
 - System Integration – 8 weeks, mid-January
 - Design Verification – 4 weeks, mid-February
 - Design Review – 1 week, late February
 - Submission – 1 week, early March
 - Tape-out in March 2027

Relevant task in MOST3

■ 课题2：硅像素探测器和无线数据传输技术

- **Vertex detector prototype:** position resolution 3 μm , time stamp precision 100 ns, power consumption 100 mW/cm²
- HVCMOS tracker prototype: position resolution 10 μm , time stamp precision 10 ns, power consumption 200 mW/cm²
- Wireless data transmission: total data rate > 30 Gbps

Proposal of the design name

- Pixelated Resolution-Enhanced CMOS Imaging Sensor (PRECIS)
- 含义解析：
 - PRECIS：取自英语单词 “Precision”（精确）和 “Precise”，体现了粒子物理实验对高精度的极致追求。
 - Pixelated：强调像素化成像能力。
 - Resolution-Enhanced：突出了高空间分辨率的优势。
 - 优势：简洁明了，直接用名字为探测器的质量背书。